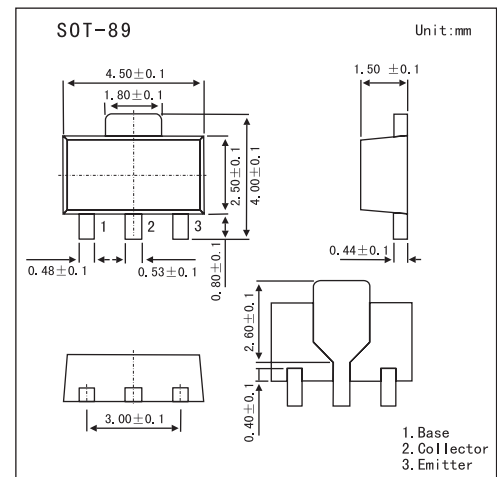


NPN Epitaxial Silicon Transistor

KSC2881

■ Features

- Collector-Emitter Voltage : $V_{CEO}=120V$
- Current Gain Bandwidth Product : $f_T=120MHz$
- Collector Dissipation : $P_C=1$ to $2W$ in Mounted on Ceramic Board

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	800	mA
Base Current	I_B	160	mA
Collector Power Dissipation	P_C	500	mW
	P_{C^*}	1,000	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{STG}	-55 to +150	$^\circ C$

* Mounted on Ceramic Board (250mm²X0.8mm)

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=10\mu A, I_B=0$	120			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=1mA, I_C=0$	5			V
Collector Cut-off Current	I_{CBO}	$V_{CB}=120V, I_E=0$			100	nA
Emitter Cut-off Current	I_{EBO}	$V_{BE}=5V, I_C=0$			100	nA
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=100mA$	80		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$			1.0	V
Base-Emitter On Voltage	$V_{BE(on)}$	$V_{CE}=5V, I_C=500mA$			1.0	V
Current Gain Bandwidth Product	f_T	$V_{CE}=5V, I_C=100mA$		120		MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$			30	pF

■ h_{FE} Classification

Marking	SCO	SCY
Rank	O	Y
Type	80~160	120~240